

LAPT 2SA1386/1386A

Silicon PNP Epitaxial Planar Transistor (Complement to type 2SC3519/A)

Application : Audio and General Purpose

Absolute maximum ratings (Ta=25°C)

Symbol	2SA1386	2SA1386A	Unit
V _{CBO}	-160	-180	V
V _{CEO}	-160	-180	V
V _{EBO}	-5		V
I _C	-15		A
I _B	-4		A
P _C	130(T _C =25°C)		W
T _j	150		°C
T _{stg}	-55 to +150		°C

Electrical Characteristics (Ta=25°C)

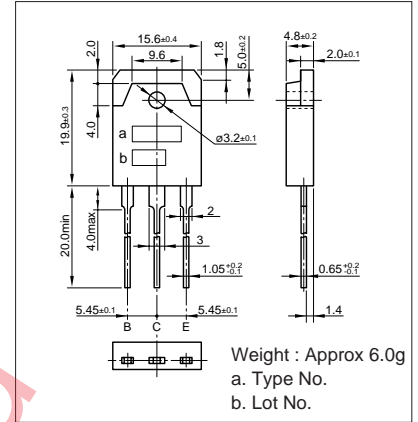
Symbol	Conditions	2SA1386	2SA1386A	Unit
I _{CBO}	V _{CB} =	-100max	-100max	μA
V _{CEO}	V _{CB} =	-160	-180	V
I _{EBO}	V _{EB} =-5V		-100max	μA
V _{(BR)CEO}	I _C =-25mA	-160min	-180min	V
h _{FE}	V _{CE} =-4V, I _C =-5A		50min*	
V _{CE(sat)}	I _C =-5A, I _B =-0.5A		-2.0max	V
f _T	V _{CE} =-12V, I _E =2A		40typ	MHz
COB	V _{CB} =-10V, f=1MHz		500typ	pF

*h_{FE} Rank: O(50 to 100), P(70 to 140), Y(90 to 180)

Typical Switching Characteristics (Common Emitter)

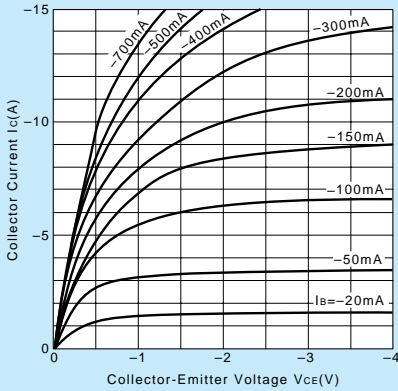
V _{CC} (V)	R _L (Ω)	I _C (A)	V _{BB1} (V)	V _{BB2} (V)	I _{B1} (A)	I _{B2} (A)	t _{on} (μs)	t _{stg} (μs)	t _f (μs)
-40	4	-10	-10	5	-1	1	0.3typ	0.7typ	0.2typ

External Dimensions MT-100(TO3P)

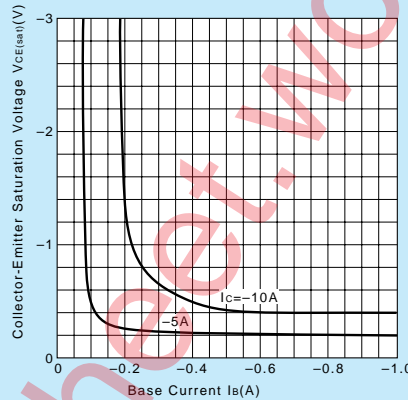


Weight : Approx 6.0g
a. Type No.
b. Lot No.

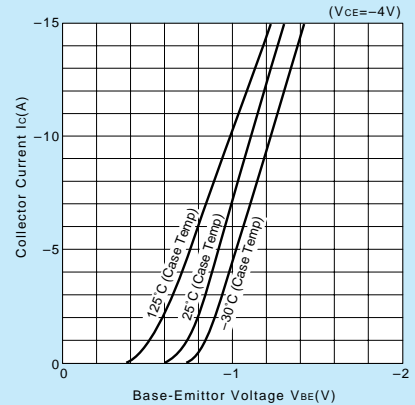
I_C-V_{CE} Characteristics (Typical)



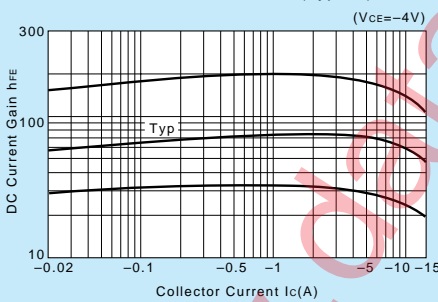
V_{CE(sat)}-I_B Characteristics (Typical)



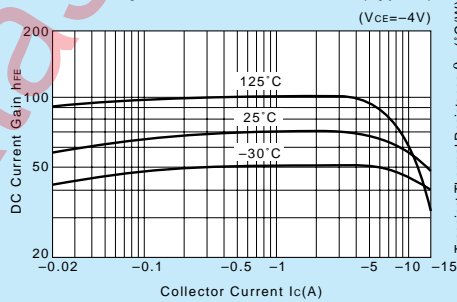
I_C-V_{BE} Temperature Characteristics (Typical)



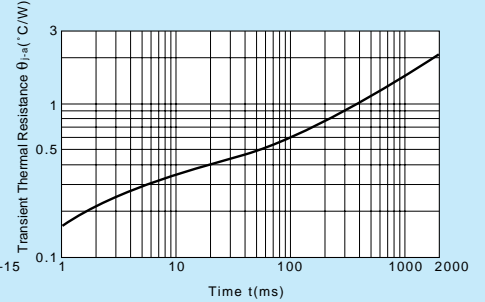
h_{FE}-I_C Characteristics (Typical)



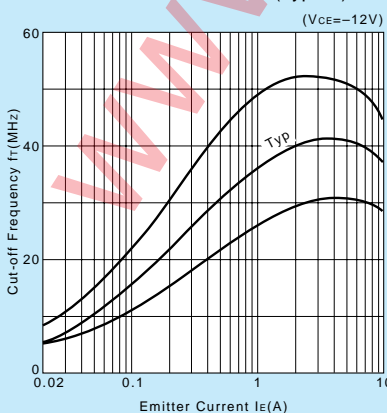
h_{FE}-I_C Temperature Characteristics (Typical)



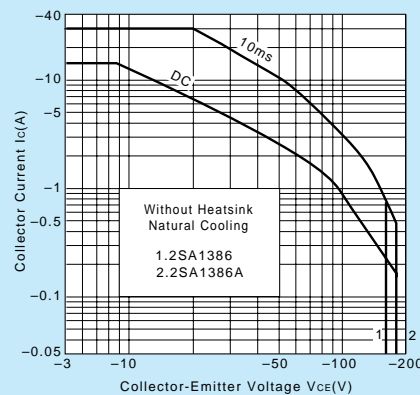
θ_{j-a}-t Characteristics



f_T-I_E Characteristics (Typical)



Safe Operating Area (Single Pulse)



P_C-T_a Derating

